

Amendments to the Claims:

1. (Currently amended) A high-density plasma CVD process comprising the steps of:

a) preparing a semiconductor substrate;
b) loading the semiconductor substrate into a process chamber; and
c) injecting first main process gases including a silicon source gas, an oxygen gas, a nitrogen free chemical etching gas and a hydrogen gas into the process chamber to generate a high density plasma over the semiconductor substrate and to simultaneously form a silicon oxide layer on the semiconductor substrate;

d) injecting second main process gases into the process chamber after the injection of the first main process gases, wherein the second main process gases include a silicon source gas, an oxygen gas, a nitrogen free chemical etching gas, a hydrogen gas and a helium gas; and

e) injecting third main process gases into the process chamber after the injection of the second main process gases, wherein the third main process gases include a silicon source gas, an oxygen gas and a hydrogen gas, wherein the semiconductor substrate is heated to a temperature in a range of about 550°C to about 700°C.

2. (original) The high-density plasma CVD process according to claim 1, wherein the high density plasma is generated by applying a plasma power to an induction coil installed outside the process chamber and a bias power to the semiconductor substrate during the injection of the first main process gases.

3. (original) The high-density plasma CVD process according to claim 2, wherein the plasma power is in the range of about 2500 to about 5000 watts and the bias power is in the range of about 800 to about 4000 watts.

4. (original) The high-density plasma CVD process according to claim 1, wherein the silicon source gas is a silane (SiH_4) gas or a disilane (Si_2H_6) gas, and the nitrogen free chemical etching gas is a silicon fluoride (SiF_4) gas.

5. (original) The high-density plasma CVD process according to claim 1, further comprising the step of injecting preliminary process gases into the process chamber prior to the injection of the first main process gases to generate a high density plasma over the semiconductor substrate and to simultaneously form an initial silicon oxide layer on the semiconductor substrate, wherein the preliminary process gases include a silicon source gas, an oxygen gas and a helium gas.

6-9. (Canceled)

10. (Currently amended) The high-density plasma CVD process according to claim 91, further comprising the step of injecting preliminary process gases into the process chamber after the injection of the third main process gases, wherein the preliminary process gases include a silicon source gas, an oxygen gas and a helium gas.

11-12. (Canceled)

13. (Currently amended) A high density plasma CVD process comprising the steps of:

- a) preparing a semiconductor substrate;
- b) loading the semiconductor substrate into a process chamber; and
- c) injecting first main process gases including a silicon source gas, an oxygen gas, a nitrogen free chemical etching gas, a helium gas and a hydrogen gas into the process chamber to generate a high density plasma above the semiconductor substrate and to simultaneously form a silicon oxide layer on the semiconductor substrate;
- d) injecting second main process gases into the process chamber after the injection of the first main process gases, wherein the second main process gases include a silicon source gas, an oxygen gas, a nitrogen free chemical etching gas and a hydrogen gas; and
- e) injecting third main process gases into the process chamber after the injection of the second main process gases, wherein the third main process gases include a silicon

source gas, an oxygen gas and a hydrogen gas, wherein the semiconductor substrate is heated to a temperature in the range of about 550°C to about 700°C.

14. (Previously presented) The high-density plasma CVD process according to claim 13, wherein the high density plasma is generated by applying a plasma power to an induction coil installed outside the process chamber and a bias power to the semiconductor substrate during the injection of the first main process gases.

15. (original) The high-density plasma CVD process according to claim 14, wherein the plasma power is in a range of about 2500 to about 5000 watts and the bias power is in a range of about 800 to about 4000 watts.

16. (original) The high-density plasma CVD process according to claim 13, wherein the silicon source gas is a silane (SiH_4) gas or a disilane (Si_2H_6) gas, and the nitrogen free chemical etching gas is a silicon fluoride (SiF_4) gas.

17. (original) The high-density plasma CVD process according to claim 13, further comprising the step of injecting preliminary process gases into the process chamber prior to the injection of the first main process gases to generate a high density plasma over the semiconductor substrate and to simultaneously form an initial silicon oxide layer on the semiconductor substrate, wherein the preliminary process gases include a silicon source gas, an oxygen gas and a helium gas.

18-21. (Canceled)

22. (currently amended) The high-density plasma CVD process according to claim ~~24~~13, further comprising the step of injecting preliminary process gases into the process chamber after the injection of the third main process gases, wherein the preliminary process gases include a silicon source gas, an oxygen gas and a helium gas.

23-26. (Canceled)